

- Free-Running Read and Write Clocks Can Be Asynchronous or Coincident
- Read and Write Operations Synchronized to Independent System Clocks
- Input-Ready Flag Synchronized to Write Clock
- Output-Ready Flag Synchronized to Read Clock
- 2048 Words by 9 Bits
- Low-Power Advanced CMOS Technology
- Programmable Almost-Full/Almost-Empty Flag
- Input-Ready, Output-Ready, and Half-Full Flags
- Cascadable in Word Width and/or Word Depth
- Fast Access Times of 12 ns With a 50-pF Load
- Data Rates up to 67 MHz
- 3-State Outputs
- Package Options Include 44-Pin Plastic Leaded Chip Carrier (FN) and 64-Pin Thin Quad Flat (PAG, PM) Packages

### description

The SN74ACT7807 is a 2048-word by 9-bit FIFO with high speed and fast access times. It processes data at rates up to 67 MHz and access times of 12 ns in a bit-parallel format. Data outputs are noninverting with respect to the data inputs. Expansion is easily accomplished in both word width and word depth.

The write-clock (WRTCLK) and read-clock (RDCLK) inputs should be free running and can be asynchronous or coincident. Data is written to memory on the rising edge of WRTCLK when the write-enable (WRTEN1/DP9, WRTEN2) inputs are high and the input-ready (IR) flag output is high. Data is read from memory on the rising edge of RDCLK when the read-enable (RDEN1, RDEN2) and output-enable (OE) inputs are high and the output-ready (OR) flag output is high. The first word written to memory is clocked through to the output buffer regardless of the levels on RDEN1, RDEN2, and OE. The OR flag indicates that valid data is present on the output buffer.

The FIFO can be reset asynchronous to WRTCLK and RDCLK.  $\overline{\text{RESET}}$  must be asserted while at least four WRTCLK and four RDCLK cycles occur to clear the synchronizing registers. Resetting the FIFO initializes the IR, OR, and half-full (HF) flags low and the almost-full/almost-empty (AF/AE) flag high. The FIFO must be reset upon power up.

The SN74ACT7807 is characterized for operation from 0°C to 70°C.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS  
INSTRUMENTS**

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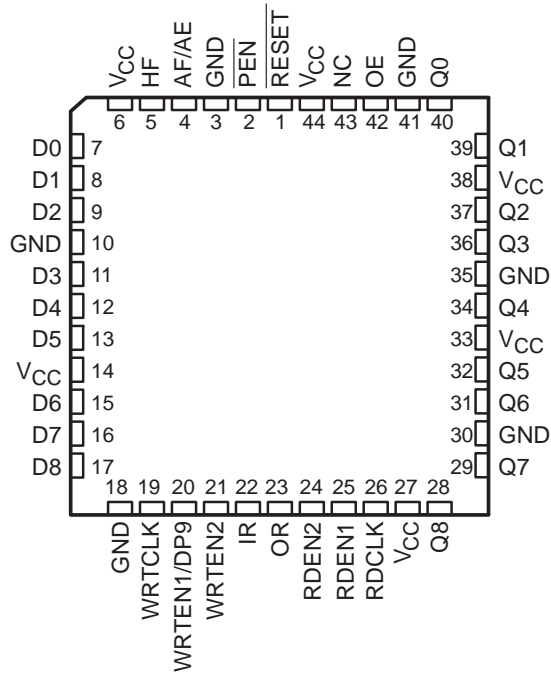
# SN74ACT7807

2048 × 9

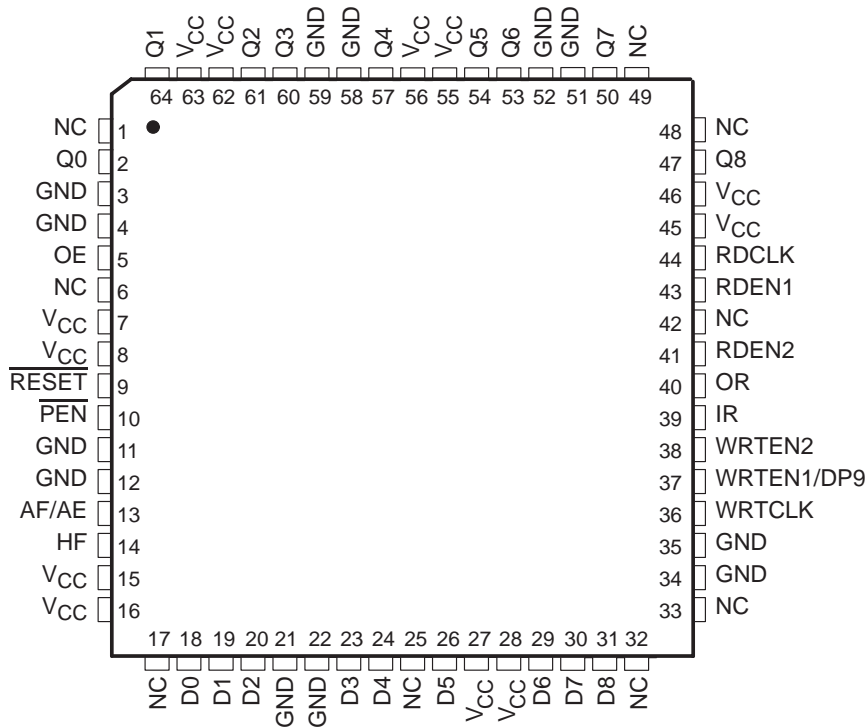
## CLOCKED FIRST-IN, FIRST-OUT MEMORY

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**FN PACKAGE  
(TOP VIEW)**



**PAG OR PM PACKAGE  
(TOP VIEW)**

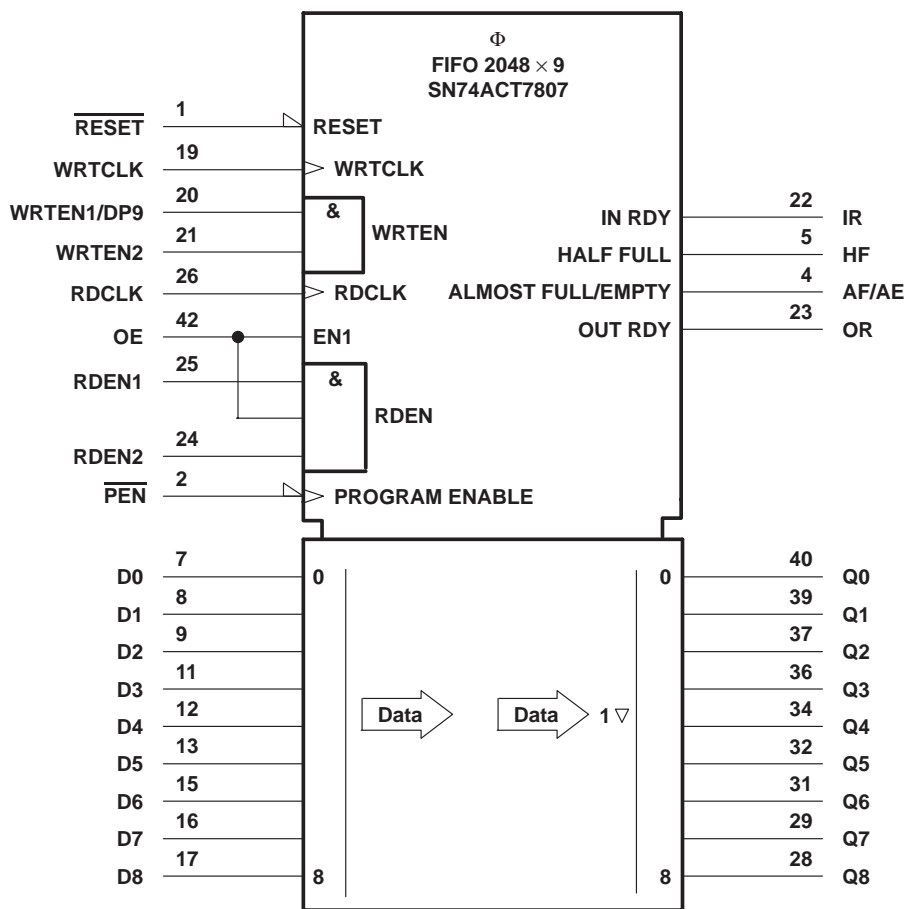


NC – No internal connection



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logic symbol†

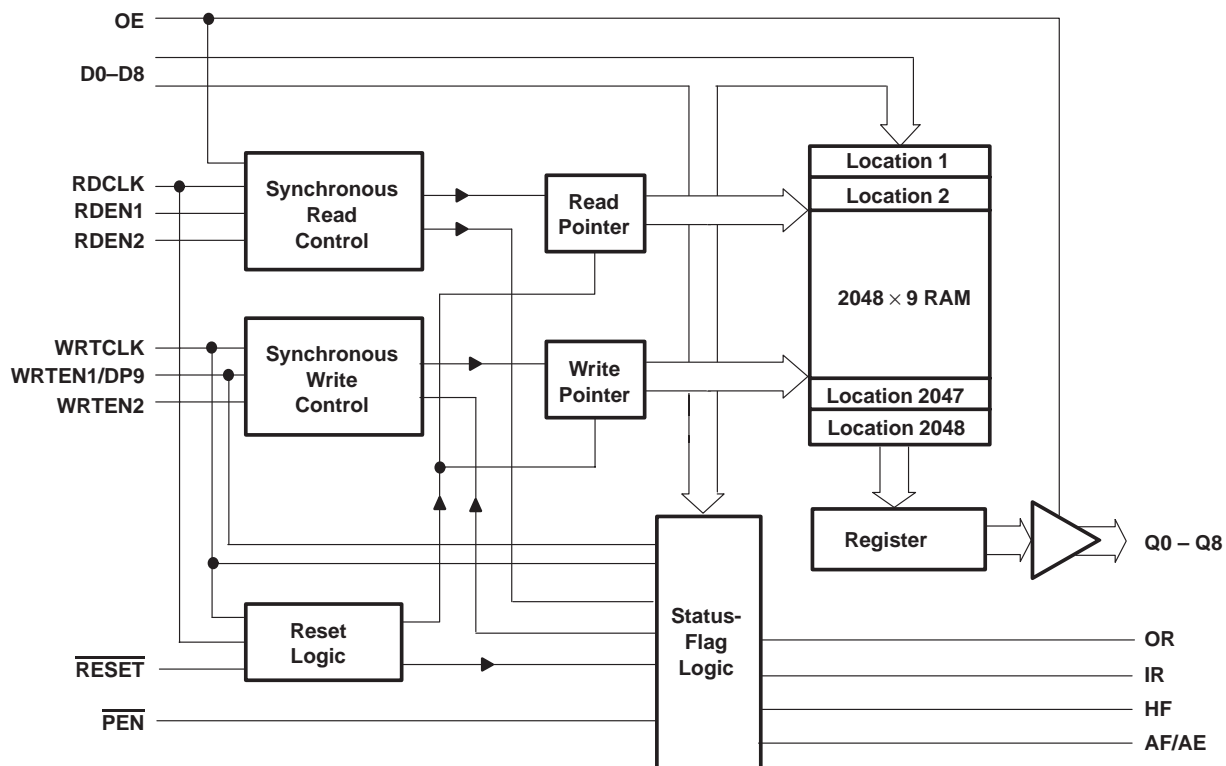


† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the FN package.

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**functional block diagram**



### Terminal Functions

TERMINAL NAME	I/O	DESCRIPTION
AF/AE	O	Almost-full/almost-empty flag. Depth offset values can be programmed for AF/AE or the default value of 256 can be used for both the almost-empty offset (X) and the almost-full offset (Y). AF/AE is high when memory contains X or fewer words or (2048 – Y) or more words. AF/AE is high after reset.
D0–D8	I	Nine-bit data input port
HF	O	Half-full flag. HF is high when the FIFO memory contains 1024 or more words. HF is low after reset.
IR	O	Input-ready flag. IR is synchronized to the low-to-high transition of WRTCLK. When IR is low, the FIFO is full and writes are disabled. IR is low during reset and goes high on the second low-to-high transition of WRTCLK after reset.
OE	I	Output enable. When OE, RDEN1, RDEN2 and OR are high, data is read from the FIFO on a low-to-high transition of RDCLK. When OE is low, reads are disabled and the data outputs are in the high-impedance state.
OR	O	Output-ready flag. OR is synchronized to the low-to-high transition of RDCLK. When OR is low, the FIFO is empty and reads are disabled. Ready data is present on Q0–Q17 when OR is high. OR is low during reset and goes high on the third low-to-high transition of RDCLK after the first word is loaded to empty memory.
$\overline{\text{PEN}}$	I	Program enable. After reset and before the first word is written to the FIFO, the binary value on D0–D8 and DP9 is latched as an AF/AE offset value when $\overline{\text{PEN}}$ is low and WRTCLK is high.
Q0–Q8	O	Nine-bit data output port. After the first valid write to empty memory, the first word is output on Q0–Q8 on the third rising edge of RDCLK. OR also is asserted high at this time to indicate ready data. When OR is low, the last word read from the FIFO is present on Q0–Q8.
RDCLK	I	Read clock. RDCLK is a continuous clock and can be asynchronous or coincident to WRTCLK. A low-to-high transition of RDCLK reads data from memory when RDEN1, RDEN2, OE, and OR are high. OR is synchronous to the low-to-high transition of RDCLK.
RDEN1 RDEN2	I	Read enables. When RDEN1, RDEN2, OE, and OR are high, data is read from the FIFO on the low-to-high transition of RDCLK.
$\overline{\text{RESET}}$	I	Reset. To reset the FIFO, four low-to-high transitions of RDCLK and four low-to-high transitions of WRTCLK must occur while $\overline{\text{RESET}}$ is low. This sets HF, IR, and OR low and AF/AE high.
WRTCLK	I	Write clock. WRTCLK is a continuous clock and can be asynchronous or coincident to RDCLK. A low-to-high transition of WRTCLK writes data to memory when WRTE1/DP9, WRTE2, and IR are high. IR is synchronous to the low-to-high transition of WRTCLK.
WRTE1/DP9	I	Write enable/data pin 9. When WRTE1/DP9, WRTE2, and IR are high, data is written to the FIFO on a low-to-high transition of WRTCLK. When programming an AF/AE offset value, WRTE1/DP9 is used as the most-significant data bit.
WRTE2	I	Write enable. When WRTE1/DP9, WRTE2, and IR are high, data is written to the FIFO on a low-to-high transition of WRTCLK.

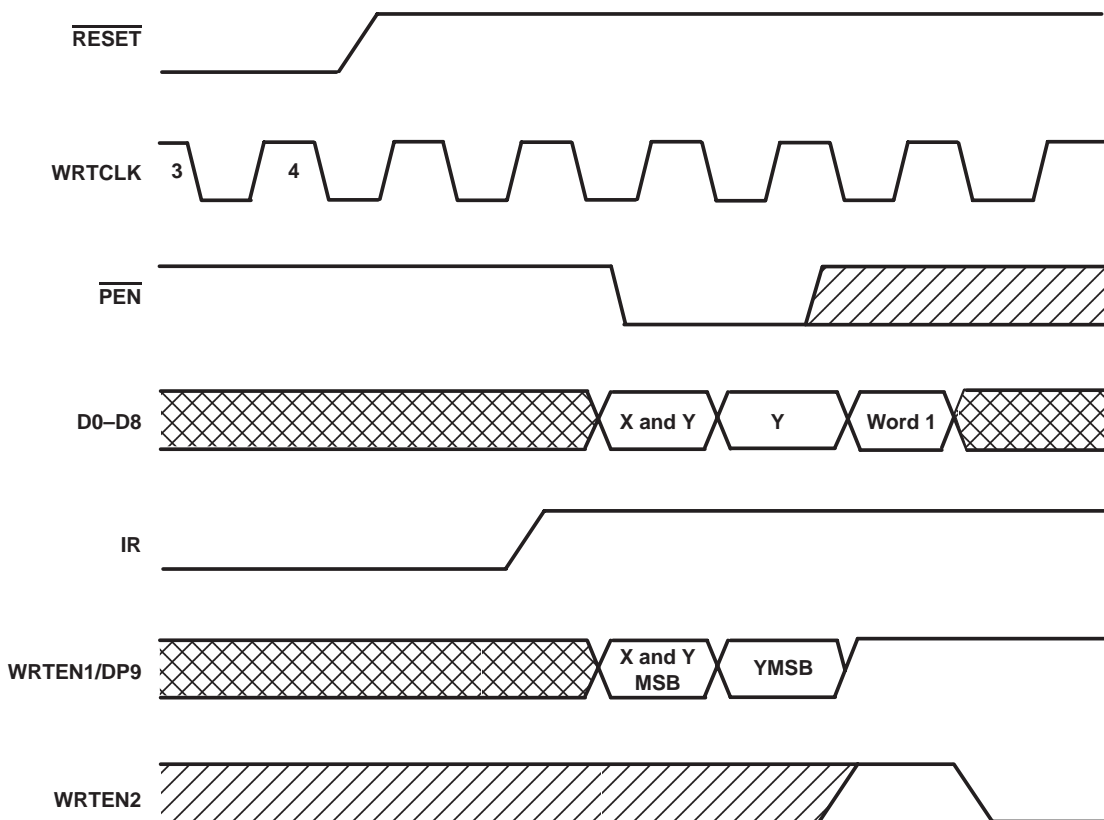
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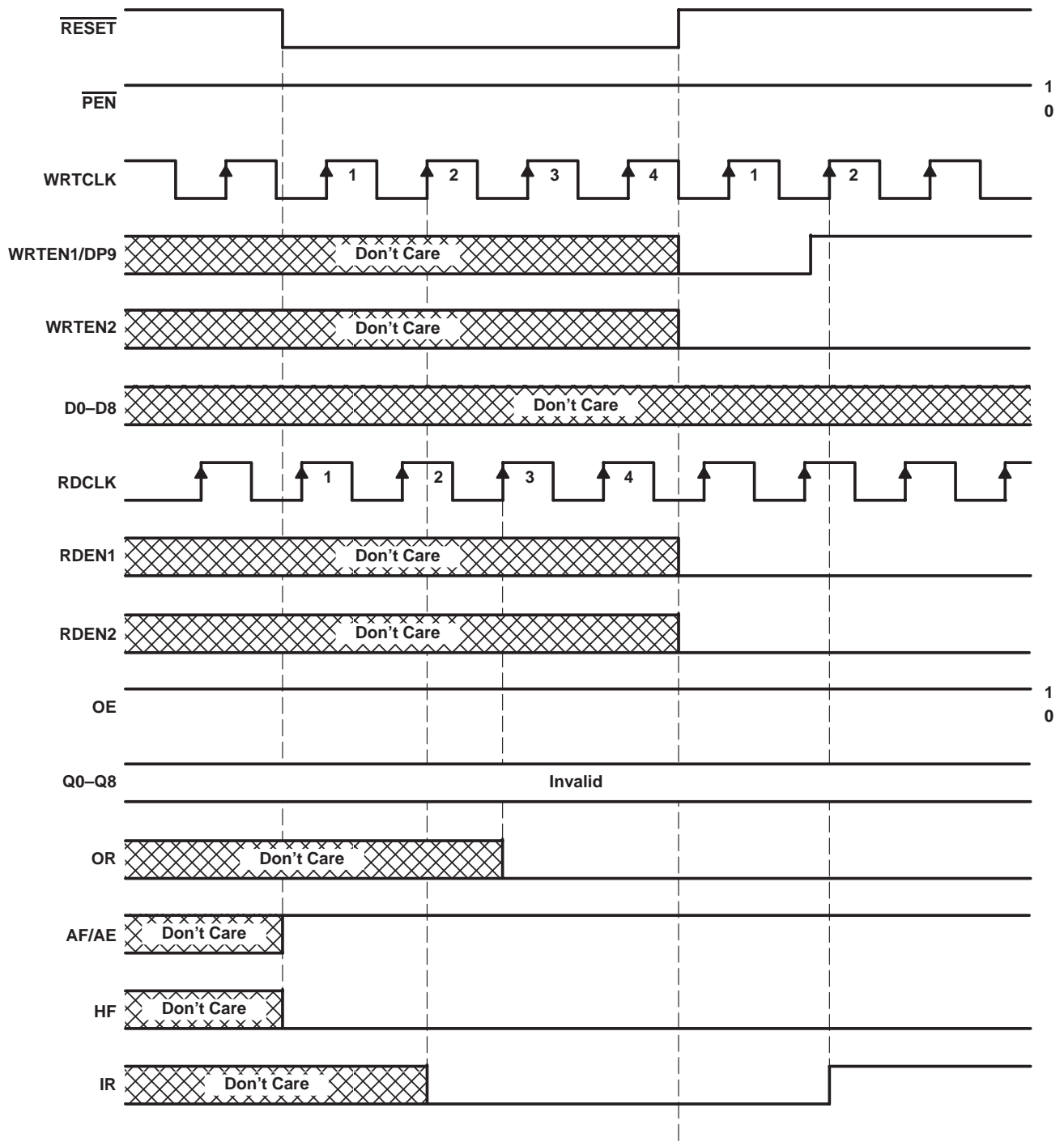
**offset values for AF/AE**

The AF/AE flag has two programmable limits: the almost-empty offset value (X) and the almost-full offset value (Y). They can be programmed after the FIFO is reset and before the first word is written to memory. If the offsets are not programmed, the default values of X = Y = 256 are used. The AF/AE flag is high when the FIFO contains X or fewer words or (2048 – Y) or more words.

Program enable ( $\overline{\text{PEN}}$ ) should be held high throughout the reset cycle.  $\overline{\text{PEN}}$  can be brought low only when IR is high and WRTCLK is low. On the following low-to-high transition of WRTCLK, the binary value on D0–D8 and WRTEN1/DP9 is stored as the almost-empty offset value (X) and the almost-full offset value (Y). Holding  $\overline{\text{PEN}}$  low for another low-to-high transition of WRTCLK reprograms Y to the binary value on D0–D8 and WRTEN1/DP9 at the time of the second WRTCLK low-to-high transition. While the offsets are programmed, data is not written to the FIFO memory, regardless of the state of the write enables (WRTEN1/DP9, WRTEN2). A maximum value of 1023 can be programmed for either X or Y (see Figure 1). To use the default values of X = Y = 256,  $\overline{\text{PEN}}$  must be held high.



**Figure 1. Programming X and Y Separately**



Define the AF/AE Flag Using the  
Default Value of X = Y = 256

**Figure 2. Reset Cycle**

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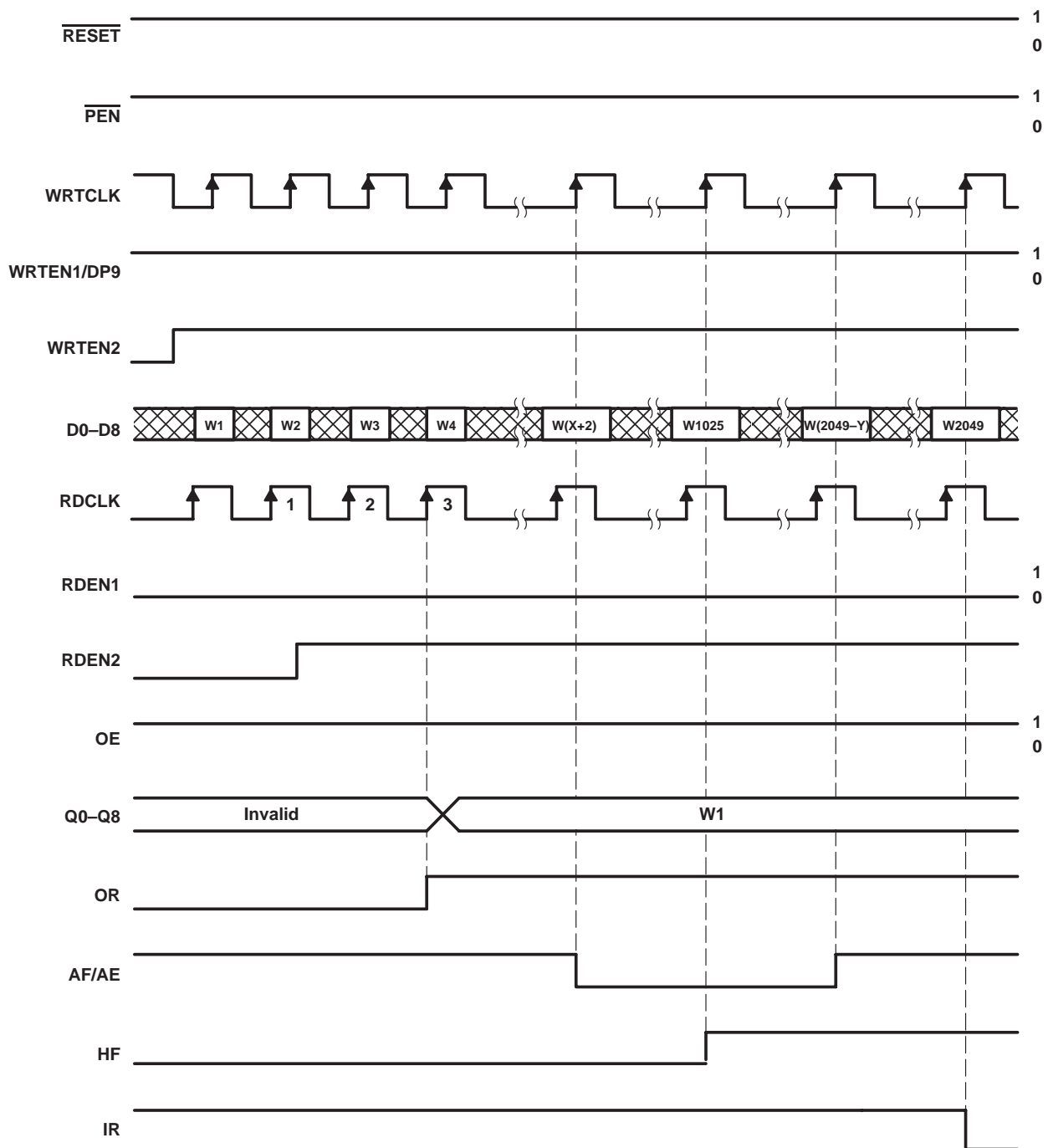
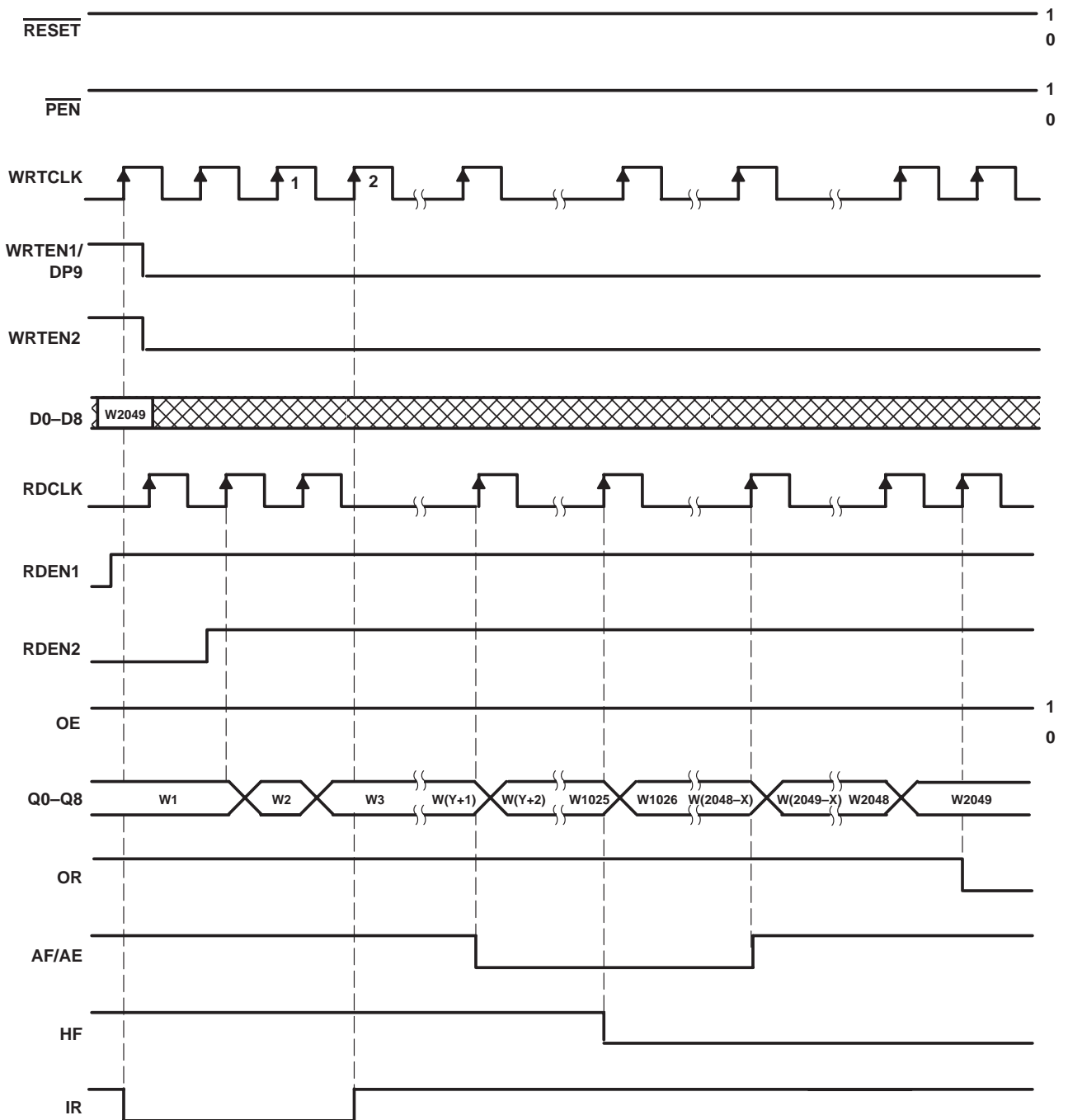


Figure 3. Write Cycle







**Figure 4. Read Cycle**

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**absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†**

Supply voltage range, $V_{CC}$ .....	-0.5 V to 7 V
Input voltage range, $V_I$ .....	-0.5 V to 7 V
Voltage range applied to a disabled 3-state output .....	-0.5 V to 5.5 V
Package thermal impedance, $\theta_{JA}$ (see Note 1): FN package .....	46°C/W
PAG package .....	58°C/W
PM package .....	67°C/W
Storage temperature range, $T_{stg}$ .....	-65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51.

**recommended operating conditions**

		'ACT7807-15		'ACT7807-20		'ACT7807-25		'ACT7807-40		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$V_{CC}$	Supply voltage	4.5	5.5	4.5	5.5	4.5	5.5	4.5	5.5	V
$V_{IH}$	High-level input voltage	2		2		2		2		V
$V_{IL}$	Low-level input voltage		0.8		0.8		0.8		0.8	V
$I_{OH}$	High-level output current	Q outputs, flags		-8	-8	-8	-8	-8	-8	mA
$I_{OL}$	Low-level output current	Q outputs		16	16	16	16	16	16	mA
		Flags		8	8	8	8	8	8	
$T_A$	Operating free-air temperature	0	70	0	70	0	70	0	70	°C

**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER		TEST CONDITIONS		MIN	TYP‡	MAX	UNIT
$V_{OH}$		$V_{CC} = 4.5\text{ V}$ ,	$I_{OH} = -8\text{ mA}$	2.4			V
$V_{OL}$	Flags	$V_{CC} = 4.5\text{ V}$ ,	$I_{OL} = 8\text{ mA}$			0.5	V
	Q outputs	$V_{CC} = 4.5\text{ V}$ ,	$I_{OL} = 16\text{ mA}$			0.5	
$I_I$		$V_{CC} = 5.5\text{ V}$ ,	$V_I = V_{CC}$ or 0			±5	µA
$I_{OZ}$		$V_{CC} = 5.5\text{ V}$ ,	$V_O = V_{CC}$ or 0			±5	µA
$I_{CC}$		$V_{CC} = 5.5\text{ V}$ ,	$V_I = V_{CC} - 0.2\text{ V}$ or 0			400	µA
$\Delta I_{CC}\text{§}$	WRTEN1/DP9	$V_{CC} = 5.5\text{ V}$ ,	One input at 3.4 V, Other inputs at $V_{CC}$ or GND			2	mA
	Other inputs					1	
$C_i$		$V_I = 0$ ,	$f = 1\text{ MHz}$			4	pF
$C_o$		$V_O = 0$ ,	$f = 1\text{ MHz}$			8	pF

‡ All typical values are at  $V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$ .

§ This is the supply current for each input that is at one of the specified TTL voltage levels rather 0 V or  $V_{CC}$ .



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**timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 5)**

		'ACT7807-15		'ACT7807-20		'ACT7807-25		'ACT7807-40		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f <sub>clock</sub>	Clock frequency	67		50		40		25		MHz
t <sub>w</sub>	Pulse duration	WRTCLK high or low		8		9		13		ns
		RDCLK high or low		8		9		13		
		PEN low		9		9		13		
t <sub>su</sub>	Setup time	D0–D8 before WRTCLK↑		5		5		5		ns
		WRTE <sub>N1</sub> , WRTE <sub>N2</sub> before WRTCLK↑		5		5		5		
		OE, RDE <sub>N1</sub> , RDE <sub>N2</sub> before RDCLK↑		6		6		6.5		
		Reset: RESE <sub>T</sub> low before first WRTCLK↑ and RDCLK↑†		7		8		8		
		PEN before WRTCLK↑		4		5		5		
t <sub>h</sub>	Hold time	D0–D8 after WRTCLK↑		0		0		0		ns
		WRTE <sub>N1</sub> , WRTE <sub>N2</sub> after WRTCLK↑		0		0		0		
		OE, RDE <sub>N1</sub> , RDE <sub>N2</sub> after RDCLK↑		0		0		0		
		Reset: RESE <sub>T</sub> low after fourth WRTCLK↑ and RDCLK↑†		5		5		5		
		PEN high after WRTCLK↓		0		0		0		
		PEN low after WRTCLK↑		3		3		3		

† To permit the clock pulse to be utilized for reset purposes

**switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C<sub>L</sub> = 50 pF (unless otherwise noted) (see Figure 5)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	'ACT7807-15			'ACT7807-20		'ACT7807-25		'ACT7807-40		UNIT
			MIN	TYP‡	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f <sub>max</sub>	WRTCLK or RDCLK		67			50		40		25		MHz
t <sub>pd</sub>	RDCLK↑	Any Q	3	9	12	3	13	3	18	3	25	ns
t <sub>pd</sub> §	RDCLK↑	Any Q	8									ns
t <sub>pd</sub>	WRTCLK↑	IR	1		9	1	12	1	14	1	16	ns
	RDCLK↑	OR	1		9	2	12	2	14	2	16	
	WRTCLK↑	AF/AE	2		16	2	20	2	25	2	30	
	RDCLK↑		2		17	2	20	2	25	2	30	
t <sub>PLH</sub>	WRTCLK↑	HF	2		19	2	21	2	23	2	25	ns
t <sub>PHL</sub>	RDCLK↑	HF	2		16	2	18	2	20	2	22	ns
t <sub>PLH</sub>	RESE <sub>T</sub> low	AF/AE	1		12	1	18	1	22	1	24	ns
t <sub>PHL</sub>	RESE <sub>T</sub> low	HF	2		12	2	18	2	22	2	24	ns
t <sub>en</sub>	OE	Any Q	2		10	2	13	2	15	2	18	ns
t <sub>dis</sub>	OE	Any Q	1		11	1	13	1	15	1	18	ns

‡ All typical values are at V<sub>CC</sub> = 5 V, T<sub>A</sub> = 25°C.

§ This parameter is measured with C<sub>L</sub> = 30 pF (see Figure 6).



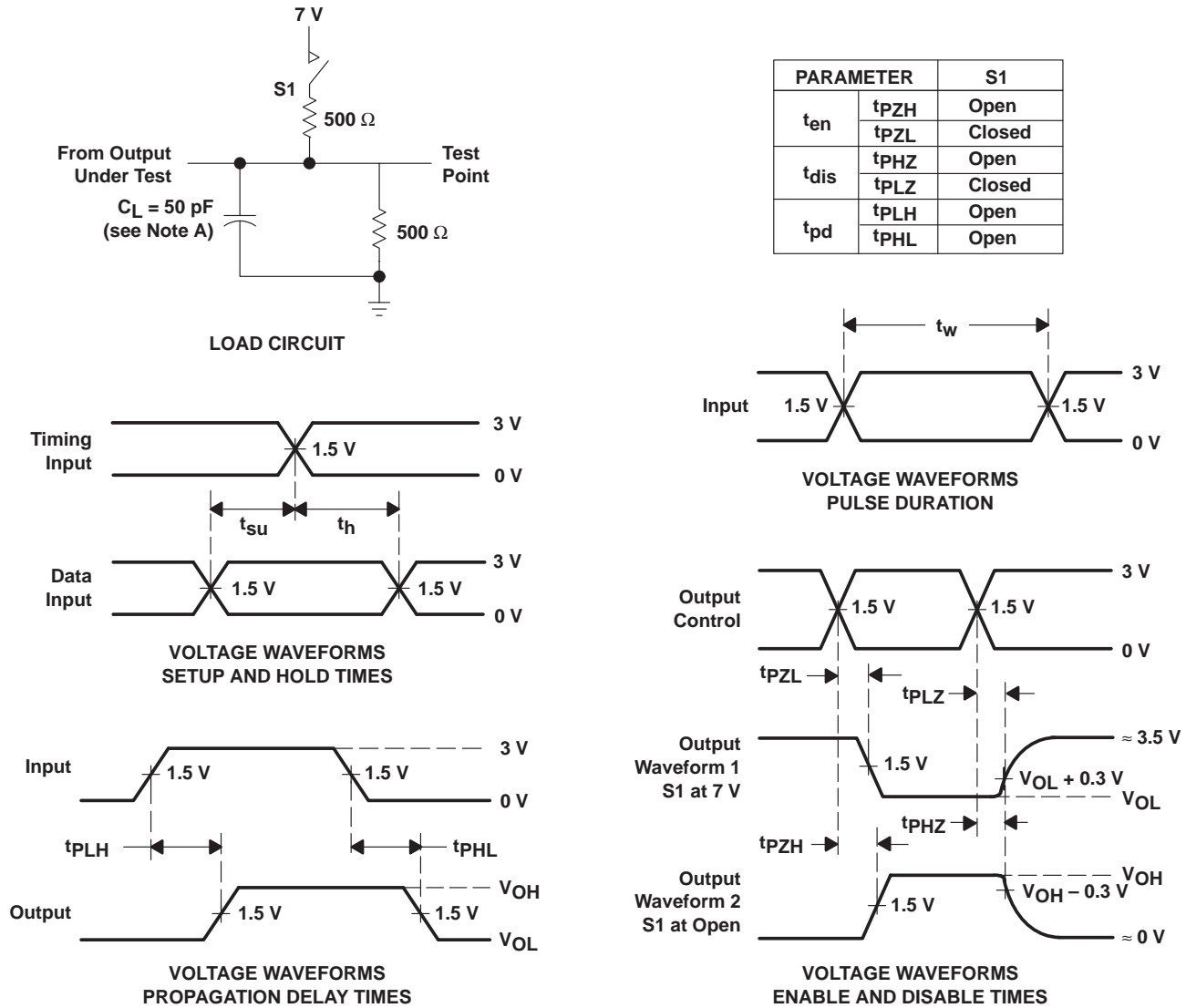
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operating characteristics,  $V_{CC} = 5\text{ V}$ ,  $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	TYP	UNIT
$C_{pd}$	Power dissipation capacitance per FIFO channel	Outputs enabled	91	pF

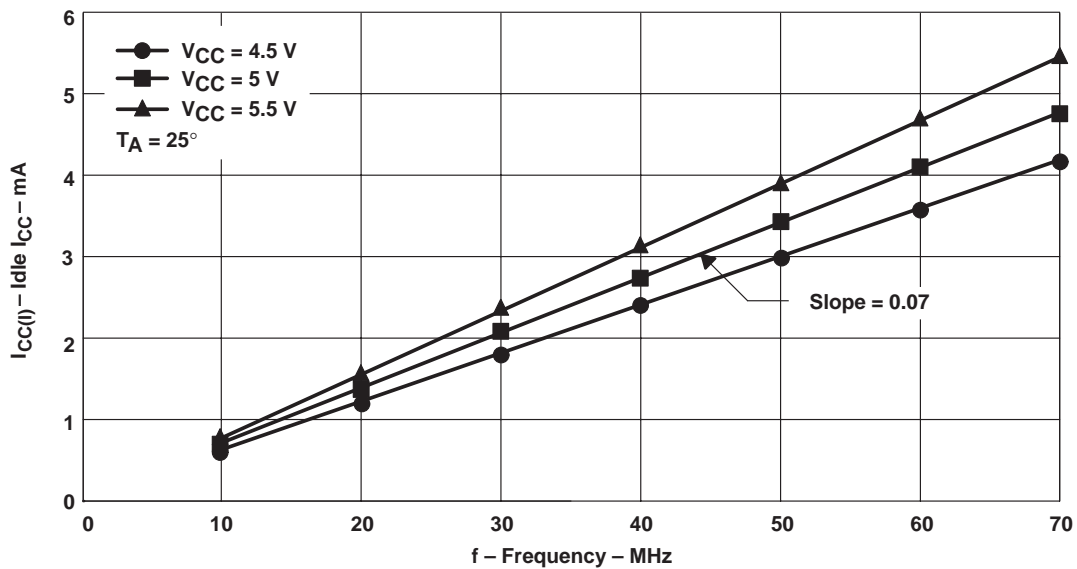
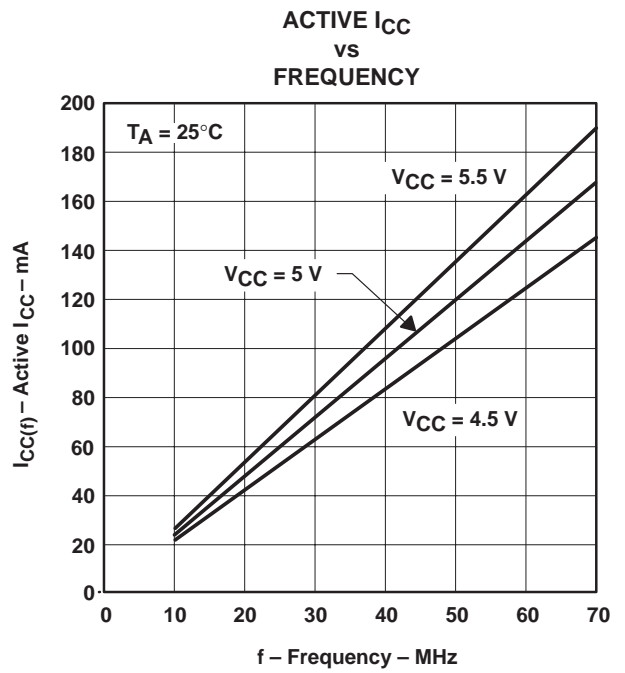
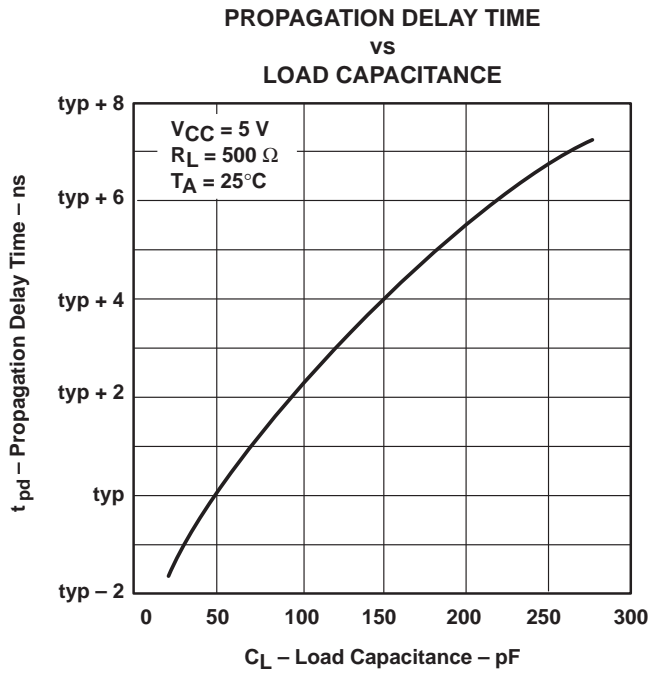
**PARAMETER MEASUREMENT INFORMATION**



NOTE A:  $C_L$  includes probe and jig capacitance.

Figure 5. Load Circuit and Voltage Waveforms

**TYPICAL CHARACTERISTICS**



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### APPLICATION INFORMATION

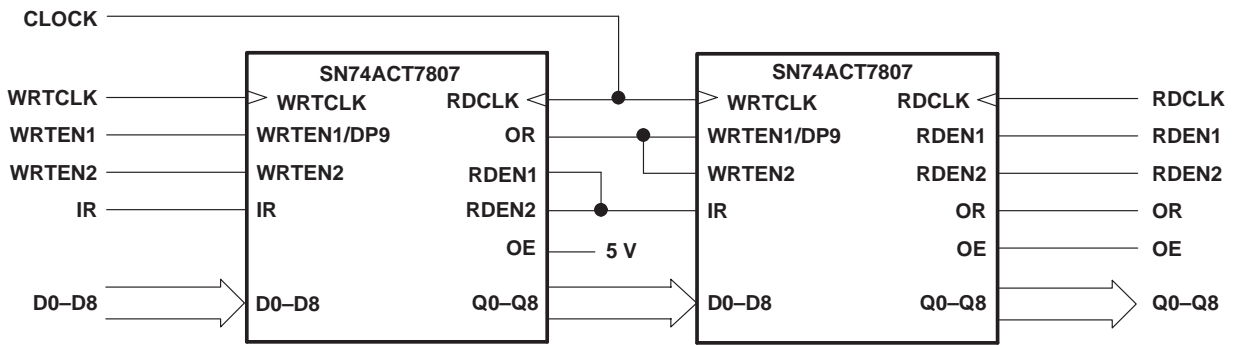


Figure 9. Word-Depth Expansion: 4096 × 9 Bits

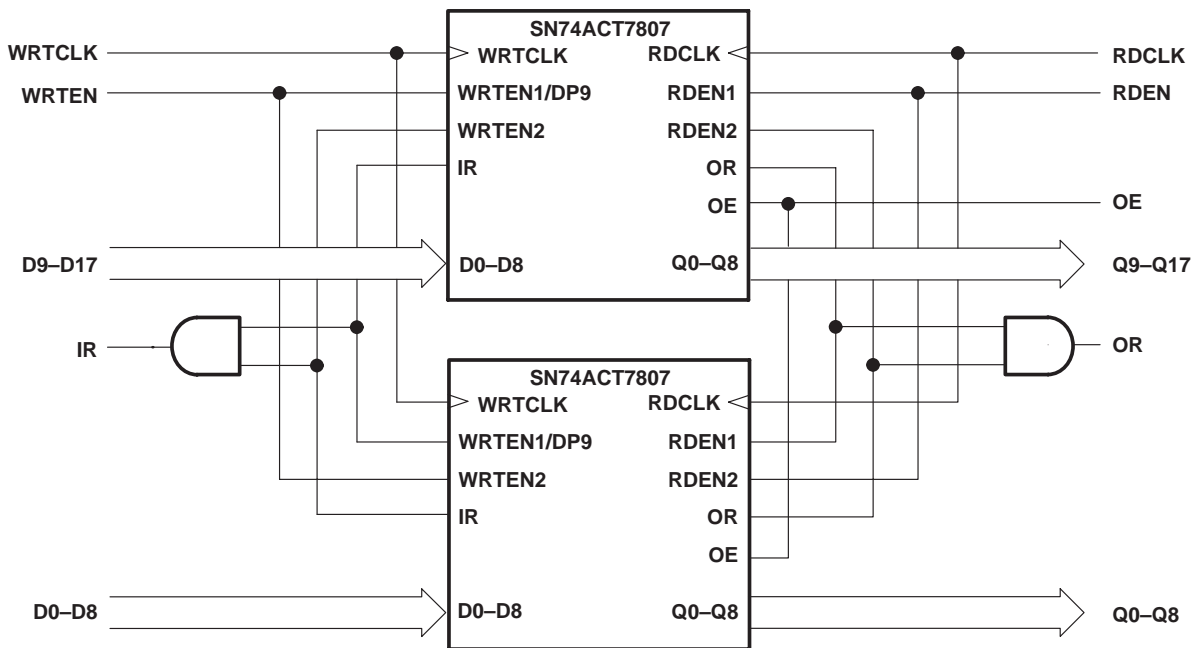


Figure 10. Word-Width Expansion: 2048 × 18 Bits

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